

Title (en)

PREPARATION OF COPPER-INDIUM-GALLIUM-DISELENIDE PRECURSOR FILMS BY ELECTRODEPOSITION FOR FABRICATING HIGH EFFICIENCY SOLAR CELLS

Title (de)

HERSTELLUNG VON KUPFER-INDIUM-DISELENIDE-AUSGANGSFOLIEN MITTELS ELEKTROBESCHICHTUNG ZUR HERSTELLUNG HOCHEFFIZIENTER SOLARZELLEN

Title (fr)

PREPARATION DE COUCHES D'UN PRECURSEUR CONSTITUE DE DISELENIURE DE CUIVRE-INDIUM-GALLIUM PAR ELECTRODEPOSITION POUR FABRIQUER DES PHOTOPILES A HAUT RENDEMENT

Publication

EP 0977911 A1 20000209 (EN)

Application

EP 98913276 A 19980330

Priority

- US 9806212 W 19980330
- US 4450697 P 19970421
- US 87008197 A 19970605

Abstract (en)

[origin: WO9848079A1] A photovoltaic cell (10) exhibiting an overall conversion efficiency of 13.6 % is prepared from a copper-indium-gallium-diselenide precursor film (18). The film (18) is fabricated by first simultaneously electrodepositing copper, indium, gallium and selenium onto a glass/molybdenum substrate (12/14). The electrodeposition voltage is a high frequency AC voltage superimposed upon a DC voltage to improve the morphology and growth rate of the film (18). The electrodeposition is followed by physical vapor deposition to adjust the final stoichiometry of the thin film (18) to approximately $\text{Cu}(\text{In}_{1-x}\text{Ga}_x)\text{Se}_2$, with the ratio of $\text{Ga}/(\text{In}+\text{Ga})$ being approximately 0.39.

IPC 1-7

C23C 28/02; H01L 21/14; H01L 21/306

IPC 8 full level

H01L 21/363 (2006.01); **H01L 21/365** (2006.01); **H01L 31/032** (2006.01); **C25D 3/56** (2006.01)

CPC (source: EP)

H01L 21/02422 (2013.01); **H01L 21/02491** (2013.01); **H01L 21/02568** (2013.01); **H01L 21/02628** (2013.01); **H01L 21/02631** (2013.01); **H01L 31/0322** (2013.01); **C25D 3/56** (2013.01); **Y02E 10/541** (2013.01)

Designated contracting state (EPC)

BE CH DE ES FR GB IT LI NL SE

DOCDB simple family (publication)

WO 9848079 A1 19981029; AU 6786998 A 19981113; CA 2284826 A1 19981029; CA 2284826 C 20070605; EP 0977911 A1 20000209; EP 0977911 A4 20020522

DOCDB simple family (application)

US 9806212 W 19980330; AU 6786998 A 19980330; CA 2284826 A 19980330; EP 98913276 A 19980330